Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±25	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_C = +25°C T_C = +70°C	I_D	30 25	A
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	8.5 6.8	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	11.3 9.1	A
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	6.6 5.3	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	8.7 7.0	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	2.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	60	A
Avalanche Current (Note 7) L = 0.1mH			I_{AS}	18	A
Avalanche Energy (Note 7) L = 0.1mH			E_{AS}	16	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_D	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	126	°C/W
	t<10s		71	
Total Power Dissipation (Note 6)		P_D	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	56	°C/W
	t<10s		31	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	7.0	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 24V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	1.7	2.1	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	16	21	mΩ	V_{GS} = 10V, I_D = 10A
		—	21	35		V_{GS} = 4.5V, I_D = 8.5A
Diode Forward Voltage	V_{SD}	0.5	—	1.2	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{ISS}	—	697	—	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{OSS}	—	97	—	pF	
Reverse Transfer Capacitance	C_{RSS}	—	67	—	pF	
Gate resistance	R_G	—	1.47	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_G	—	6.0	—	nC	V_{GS} = 10V, V_{DS} = 15V, I_D = 9A
Total Gate Charge (V_{GS} = 10V)	Q_G	—	13.2	—	nC	
Gate-Source Charge	Q_{GS}	—	2.2	—	nC	
Gate-Drain Charge	Q_{GD}	—	1.8	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	4.3	—	ns	V_{DD} = 15V, V_{GS} = 10V, R_L = 15Ω, I_D = 1A, R_G = 6Ω
Turn-On Rise Time	t_R	—	4.4	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	20.1	—	ns	
Turn-Off Fall Time	t_F	—	4.1	—	ns	
Reverse Recovery Time	T_{RR}	—	7.3	—	ns	I_F = 9A, di/dt = 500A/µs
Reverse Recovery Charge	Q_{RR}	—	7.9	—	nC	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.

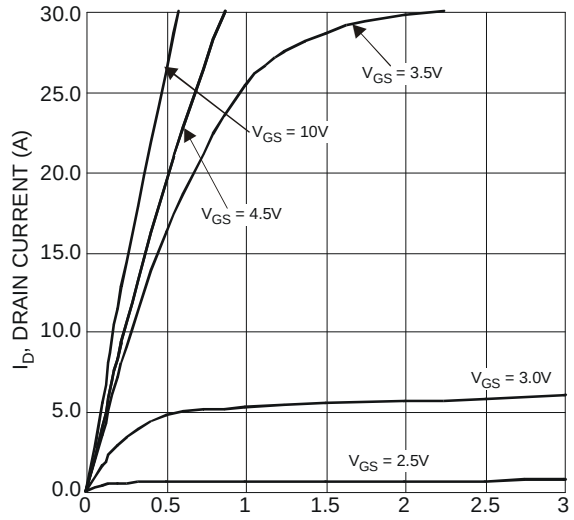


Figure 1 Typical Output Characteristics

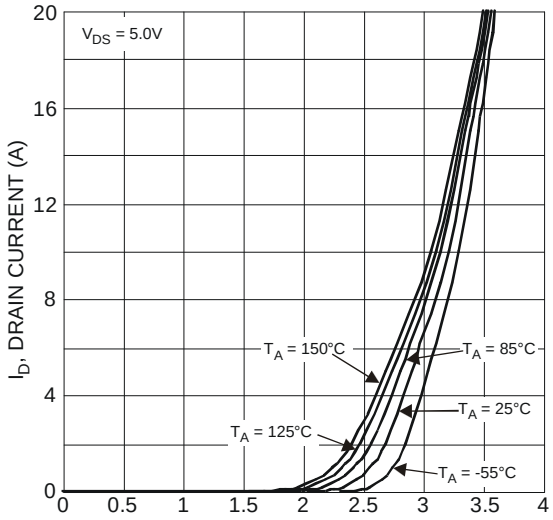


Figure 2 Typical Transfer Characteristics

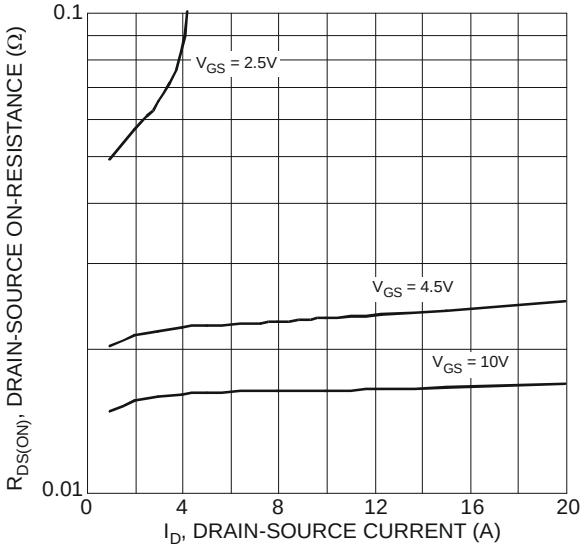


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

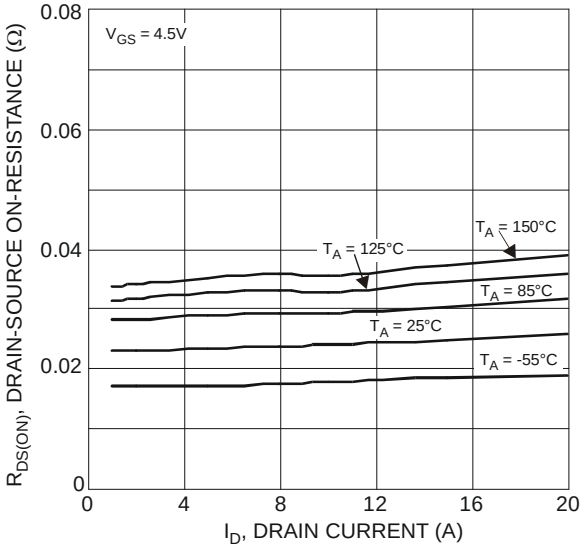


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

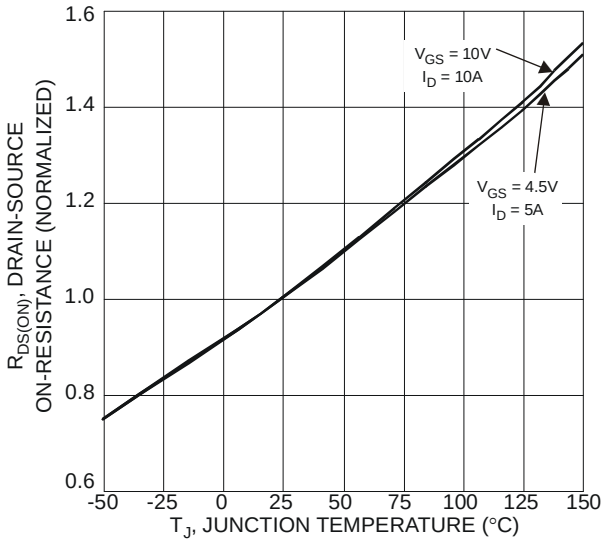


Figure 5 On-Resistance Variation with Temperature

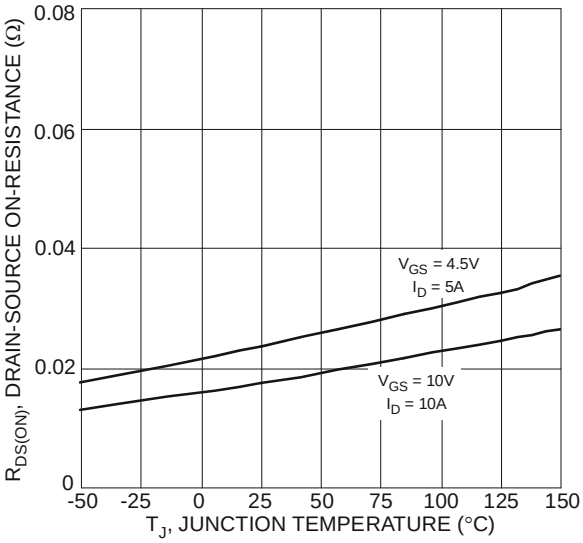


Figure 6 On-Resistance Variation with Temperature

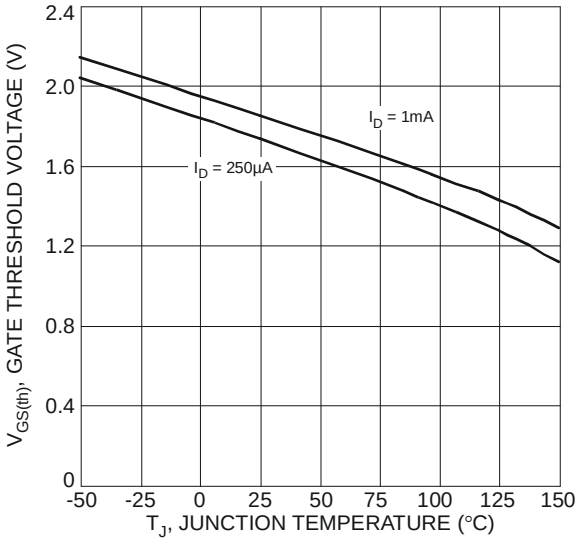


Figure 7 Gate Threshold Variation vs. Ambient Temperature

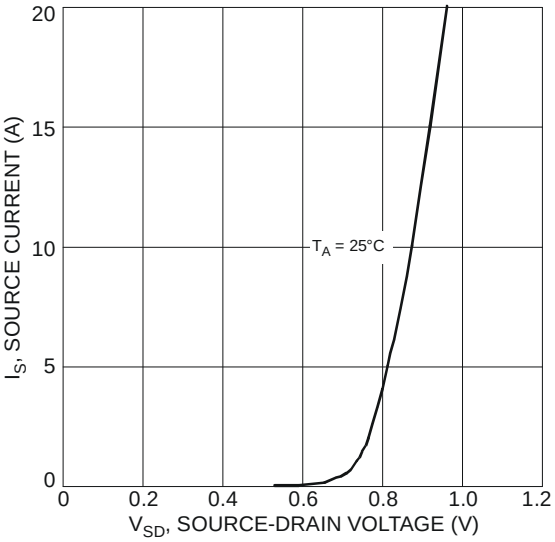


Figure 8 Diode Forward Voltage vs. Current

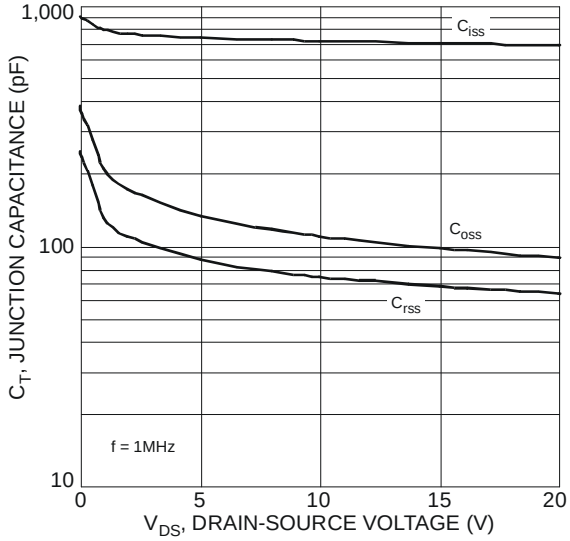


Figure 9 Typical Junction Capacitance

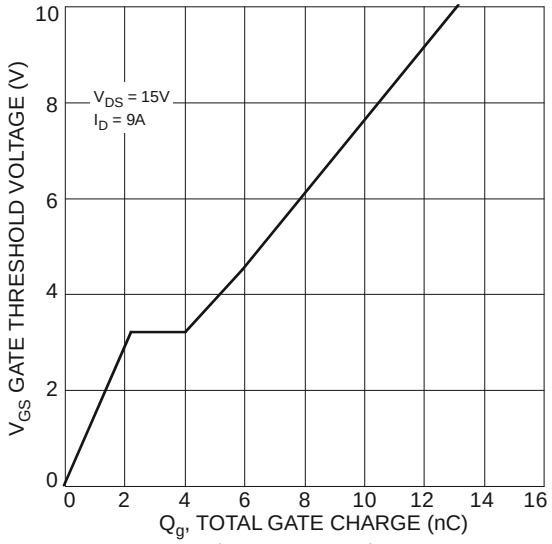


Figure 10 Gate Charge

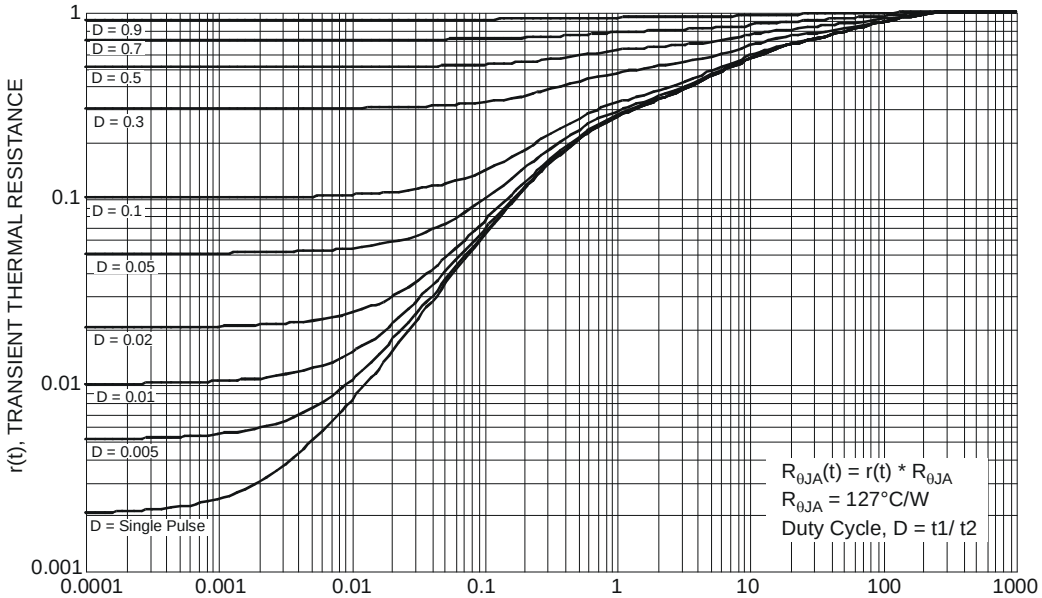
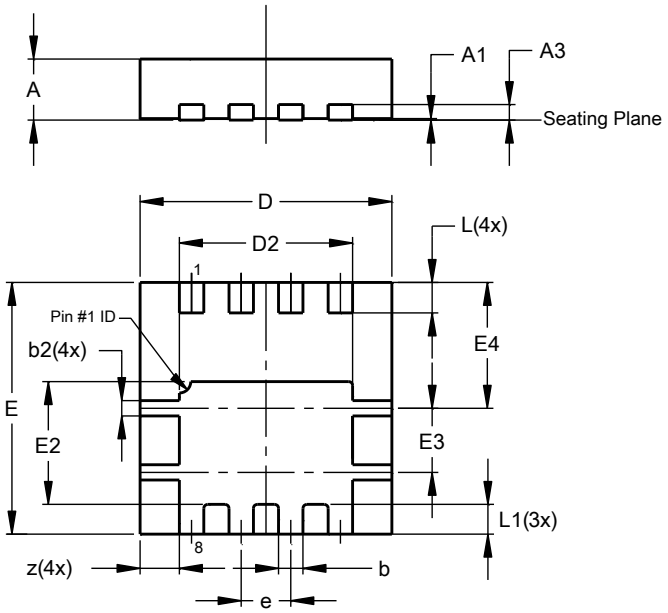


Figure 11 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

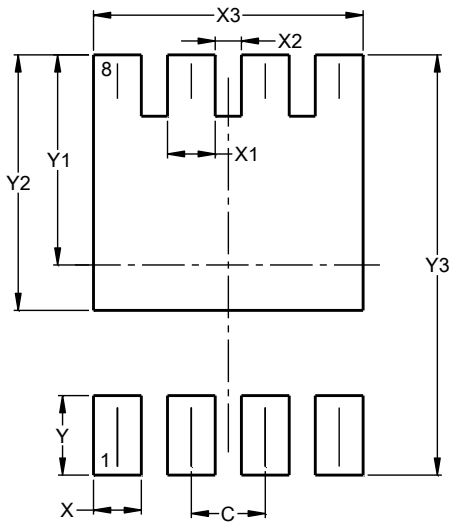


PowerDI3333-8			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	–	–	0.65
L	0.35	0.45	0.40
L1	–	–	0.39
z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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